

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	report with print with defective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/18 12:18
S1	236	fuse same semiconductor same locat\$4 same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:26
S2	82	fuse same semiconductor same locat\$4 same memory same defect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:28
S3	960	fuse with defect\$4 same semiconductor same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:29
S4	53	fuse with defect\$4 same semiconductor same memory same locat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:30
S5	6	fuse with defect\$4 same semiconductor same memory same locat\$4 and (fuse.ti.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 12:37
S6	11	("5835431" "5933376" "6008523" "6119251" "6266792" "6408401" "6477095" "6479310" "6578157" "20020085439" "20020133770"). PN.	US-PGPUB; USPAT	OR	ON	2005/01/12 12:37
S7	11	("5835431" "5933376" "6008523" "6119251" "6266792" "6408401" "6477095" "6479310" "6578157" "20020085439" "20020133770"). PN. and fuse and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 12:37
S8	7	("5835431" "5933376" "6008523" "6119251" "6266792" "6408401" "6477095" "6479310" "6578157" "20020085439" "20020133770"). PN. and fuse with defect\$4 and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 12:40
S9	566	test\$3 with fuse with defect\$5 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 12:40

S10	57	test\$3 with fuse with defect\$5 same locat\$4 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:41
S11	0	test\$3 near fuse near defect\$5 same locat\$4 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 12:42
S12	0	test\$3 near fuse near defect\$5 and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:41
S13	73	test\$3 with fuse with defect\$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:59
S14	0	(test\$3 with fuse with defect\$5).ti.	US-PGPUB; USPAT	OR	ON	2005/01/12 13:50
S15	11	(test\$3 and fuse and defect\$5).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 13:51
S16	98	test\$3 with fuse same defect\$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:57
S17	1	test\$3 near fuse same defect\$5 same plurality and memory and semiconductor	US-PGPUB; USPAT	OR	ON	2005/01/12 13:57
S18	62	test\$3 with defect\$4 near fuse and semiconductor and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 14:11
S19	66	test\$3 with defect\$4 near fuse and memory	US-PGPUB; USPAT	OR	ON	2005/01/12 14:06
S20	2	test\$3 with defect\$4 near fuse and semiconductor and memory	USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 14:16
S21	54	test\$3 near fuse with defect\$4 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 14:18
S22	82	(defect defective) near fuse same test\$3 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:09
S23	64	(defect defective) near fuse with test\$3 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:09

S24	2	(defect defective) near fuse near test\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:12
S25	30	(defect defective) near fuse same test\$3 same (semiconductor die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:14
S26	30	(defect defective) near fuse same test\$3 same (semiconductor die wafer) and fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 15:19
S27	17	(faulty broken) near fuse same test\$3 same (semiconductor die wafer) and fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S28	57	fuse near evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S29	17	fuse near evaluat\$4 and semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/12 17:21
S30	0	test\$3 same common near location same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:26
S31	522	test\$3 same plurality same location same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:27
S32	233	test\$3 same plurality same location same semiconductor with device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:27
S33	20	test\$3 same plurality same location same semiconductor with device same defect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 11:28

S34	12	test\$3 same plurality with semiconductor with device same location same defect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 16:31
S35	0	ouput near report same (faulty deenerate defective) same fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53
S36	0	ouput near report same (faulty deenerate defective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53
S37	0	ouput near report same (faulty degenerate defective)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 12:53
S38	0	test\$3 same plurality with semiconductor with device same location same defect\$4 and report	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/13 16:31